

2MBI550VJ-170-50

IGBT Modules

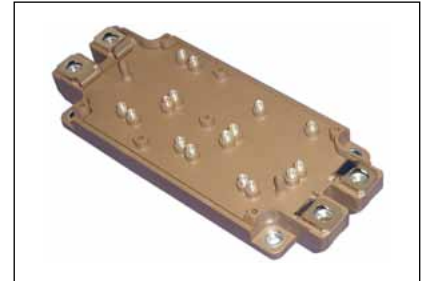
IGBT MODULE (V series) 1700V / 550A / 2 in one package

■ Features

- High speed switching
- Voltage drive
- Low Inductance module structure

■ Applications

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply
- Industrial machines, such as Welding machines



■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings (at T_c=25°C unless otherwise specified)

Items	Symbols	Conditions	Maximum ratings	Units	
Inverter	Collector-Emitter voltage	V _{CEs}	1700	V	
	Gate-Emitter voltage	V _{GES}	±20	V	
	Collector current	I _c	Continuous	T _c =25°C 750 T _c =100°C 550	A
		I _{c pulse}	1ms	1100	
		-I _c		550	
Collector power dissipation	P _c	1 device	1100	W	
Junction temperature	T _j		3750		
Operating junction temperature (under switching conditions)	T _{top}		175	°C	
Storage temperature	T _{stg}		150		
Isolation voltage	between terminal and copper base (*1) between thermistor and others (*2)	V _{iso}	-40 ~ 125	VAC	
			AC : 1min.		
Screw torque	Mounting (*3)	-	3400	N m	
	Terminals (*4)	-	3.5		
	PC-Board (*5)	-	4.5		
			0.6		

Note *1: All terminals should be connected together during the test.

Note *2: Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

Note *3: Recommendable Value : 2.5-3.5 Nm (M5)

Note *4: Recommendable Value : 3.5-4.5 Nm (M6)

Note *5: Recommendable Value : 0.4-0.6 Nm (M2.5)

● Electrical characteristics (at T_j = 25°C unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units	
			min.	typ.	max.		
Zero gate voltage collector current	I _{CEs}	V _{GE} = 0V, V _{CE} = 1700V	-	-	3.0	mA	
Gate-Emitter leakage current	I _{GES}	V _{CE} = 0V, V _{GE} = ±20V	-	-	600	nA	
Gate-Emitter threshold voltage	V _{GE(th)}	V _{CE} = 20V, I _c = 550mA	6.0	6.5	7.0	V	
Collector-Emitter saturation voltage	V _{CE(sat)} (terminal)	V _{GE} = 15V I _c = 550A	T _j =25°C	-	3.00	3.45	V
			T _j =125°C	-	3.55	-	
	T _j =150°C		-	3.60	-		
	T _j =25°C		-	2.15	2.60		
	T _j =125°C		-	2.70	-		
V _{CE(sat)} (chip)	T _j =150°C	-	2.80	-			
Internal gate resistance	R _{g(int)}	-	-	1.67	-	Ω	
Input capacitance	C _{ies}	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz	-	40	-	nF	
Turn-on time	t _{on}	V _{CC} = 900V	-	1000	-	nsec	
	t _r	I _c = 550A	-	500	-		
	t ₍₀₎	V _{GE} = ±15V	-	120	-		
Turn-off time	t _{off}	R _G = 3.3Ω	-	1300	-	nsec	
	t _r	L _S = 80nH	-	100	-		
Forward on voltage	V _F (terminal)	V _{GE} = 0V I _F = 550A	T _j =25°C	-	2.80	3.25	V
			T _j =125°C	-	3.10	-	
	T _j =150°C		-	3.05	-		
	T _j =25°C		-	1.95	2.40		
	T _j =125°C		-	2.25	-		
V _F (chip)	T _j =150°C	-	2.20	-			
Reverse recovery time	t _{rr}	I _F = 550A	-	250	-	nsec	
Resistance	R	T = 25°C	-	5000	-	Ω	
		T = 100°C	465	495	520		
B value	B	T = 25/50°C	3305	3375	3450	K	

● Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance(1device)	$R_{th(j-c)}$	Inverter IGBT	-	-	0.04	°C/W
		Inverter FWD	-	-	0.06	
Contact thermal resistance (1device) (*6)	$R_{th(c-f)}$	with Thermal Compound	-	0.0167	-	

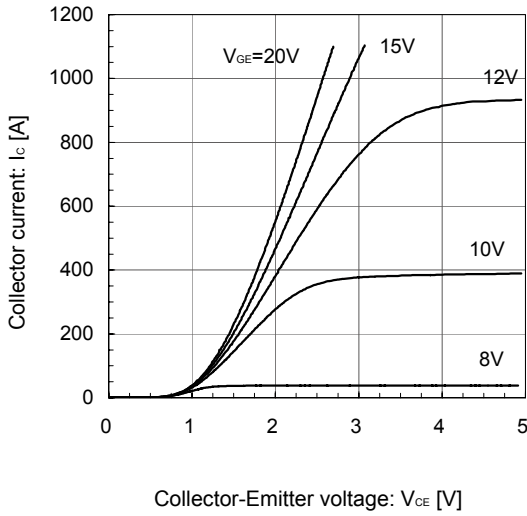
Note *6: This is the value which is defined mounting on the additional cooling fin with thermal compound.



■ Characteristics (Representative)

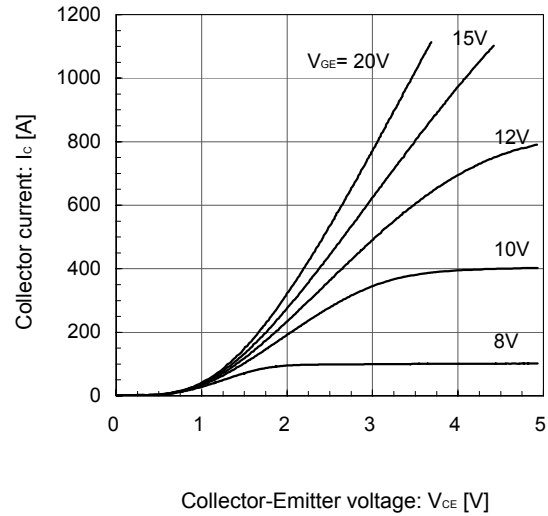
[INVERTER]

Collector current vs. Collector-Emittter voltage (typ.)
T_J = 25°C / chip



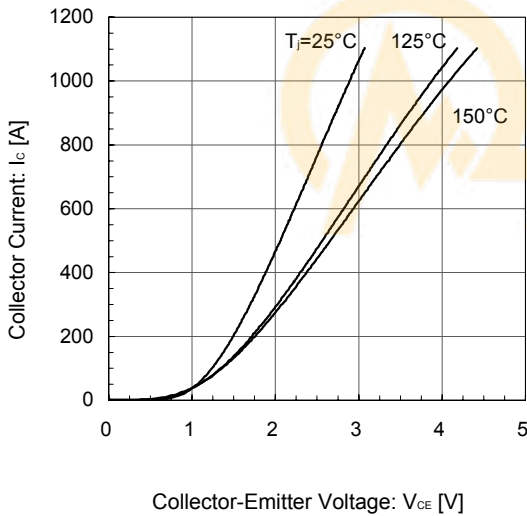
[INVERTER]

Collector current vs. Collector-Emittter voltage (typ.)
T_J = 150°C / chip



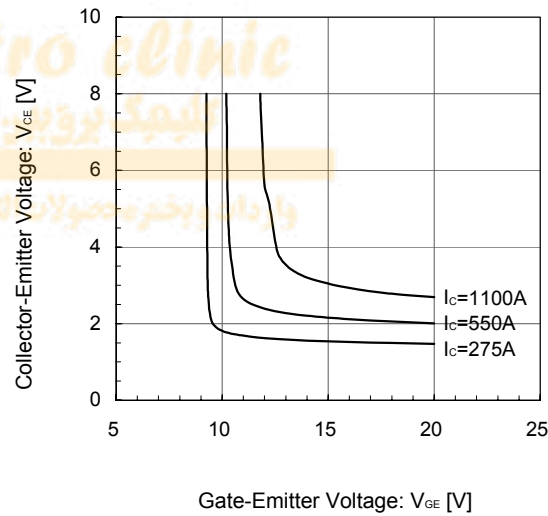
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Collector current vs. Collector-Emittter voltage (typ.)
V_{GE} = 15V / chip



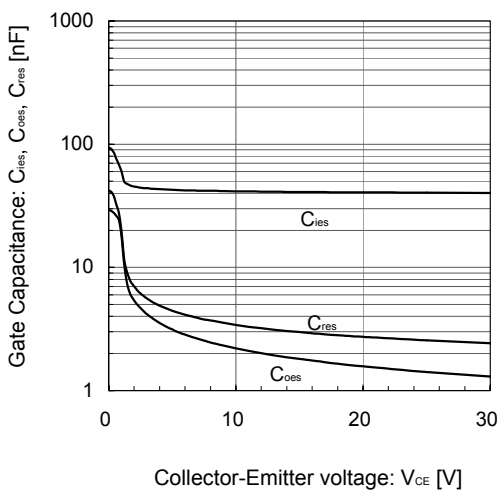
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Collector-Emittter voltage vs. Gate-Emittter voltage (typ.)
T_J = 25°C / chip



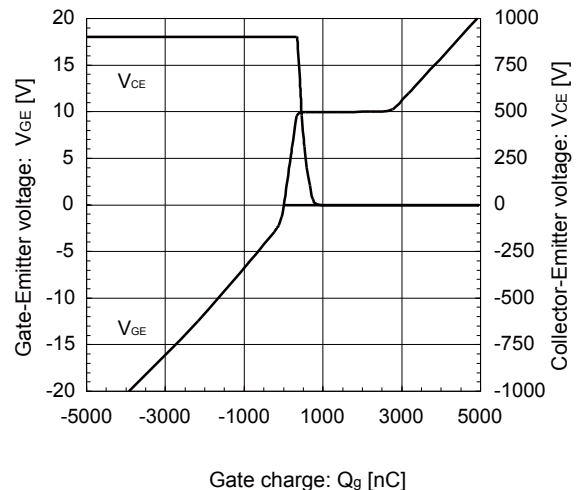
[INVERTER]

Gate Capacitance vs. Collector-Emittter Voltage (typ.)
V_{GE} = 0V, f = 1MHz, T_J = 25°C



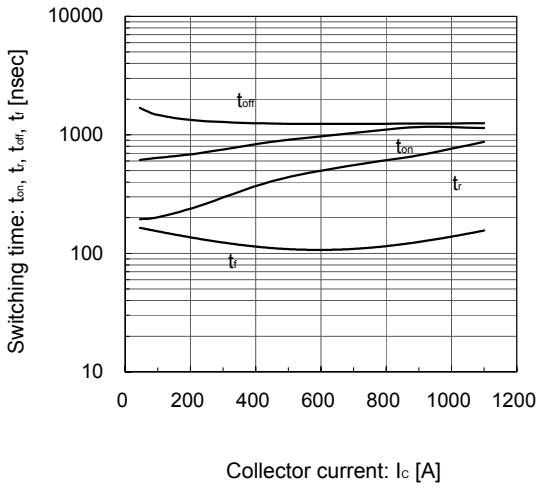
[INVERTER]

Dynamic Gate Charge (typ.)
V_{CC} = 900V, Ic = 550A, T_J = 25°C



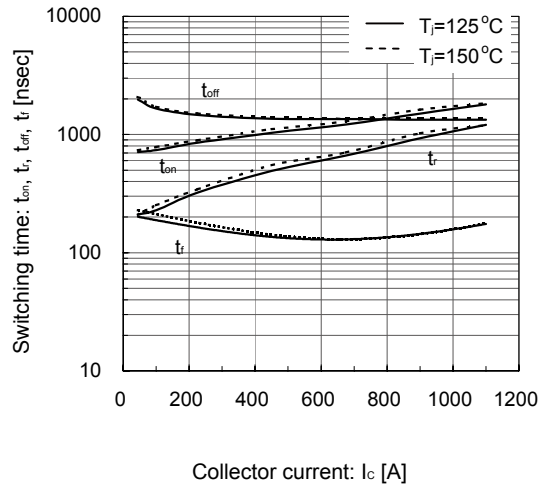
[INVERTER]

Switching time vs. Collector current (typ.)
 $V_{CC}=900V, V_{GE}=\pm 15V, R_G=3.3\Omega, T_J=25^\circ C$



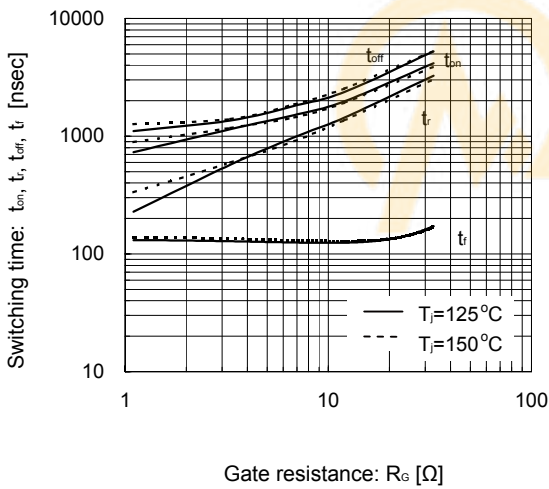
[INVERTER]

Switching time vs. Collector current (typ.)
 $V_{CC}=900V, V_{GE}=\pm 15V, R_G=3.3\Omega, T_J=125^\circ C, 150^\circ C$



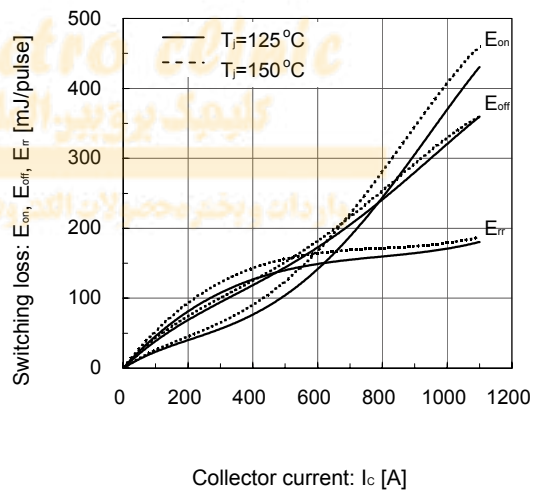
[INVERTER]

Switching time vs. Gate resistance (typ.)
 $V_{CC}=900V, I_c=550A, V_{GE}=\pm 15V, T_J=125^\circ C, 150^\circ C$



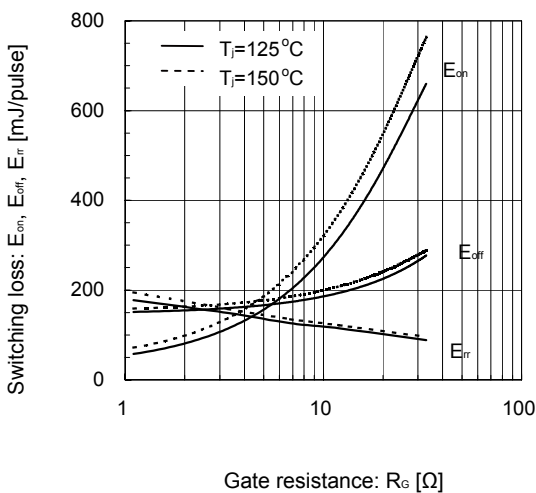
[INVERTER]

Switching loss vs. Collector current (typ.)
 $V_{CC}=900V, V_{GE}=\pm 15V, R_G=3.3\Omega, T_J=125^\circ C, 150^\circ C$



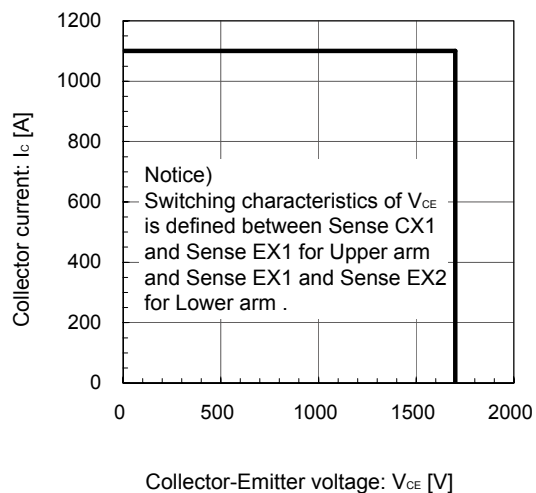
[INVERTER]

Switching loss vs. Gate resistance (typ.)
 $V_{CC}=900V, I_c=550A, V_{GE}=\pm 15V, T_J=125^\circ C, 150^\circ C$



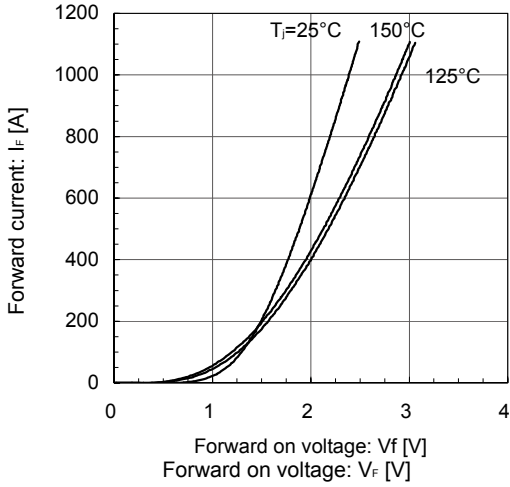
[INVERTER]

Reverse bias safe operating area (max.)
 $+V_{GE}=15V, -V_{GE}=15V, R_G=3.3\Omega, T_J=150^\circ C$



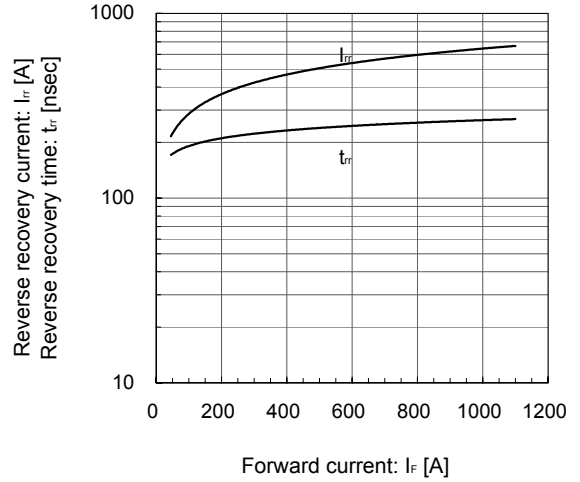
[INVERTER]

Forward Current vs. Forward Voltage (typ.)
chip



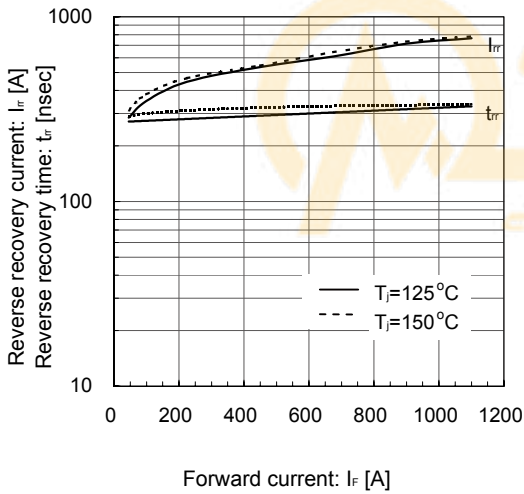
[INVERTER]

Reverse Recovery Characteristics (typ.)
 $V_{CC}=900V, V_{GE}=\pm 15V, R_G=3.3\Omega, T_J=25^\circ C$

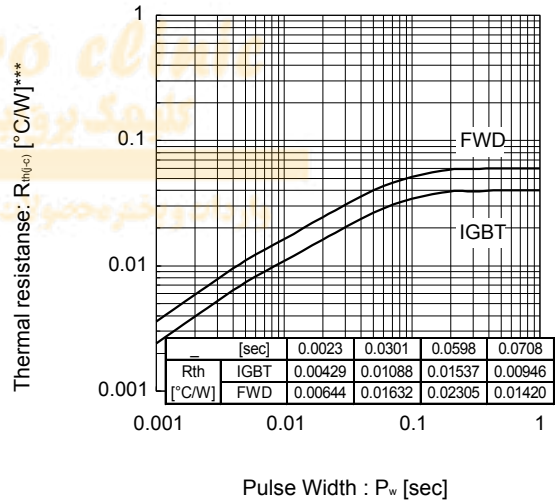


[INVERTER]

Reverse Recovery Characteristics (typ.)
 $V_{CC}=900V, V_{GE}=\pm 15V, R_G=3.3\Omega, T_J=125^\circ C, 150^\circ C$

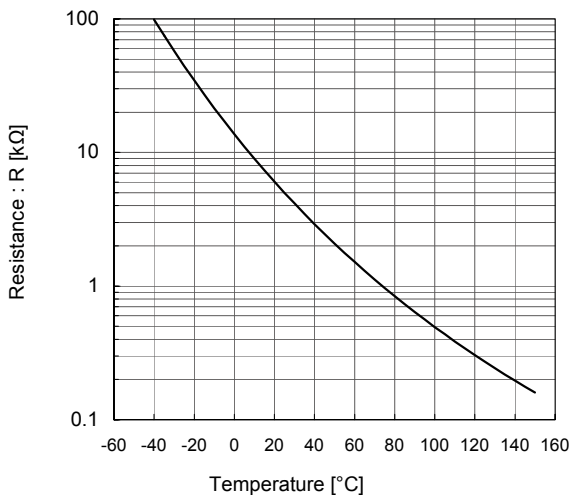


Transient Thermal Resistance (max.)



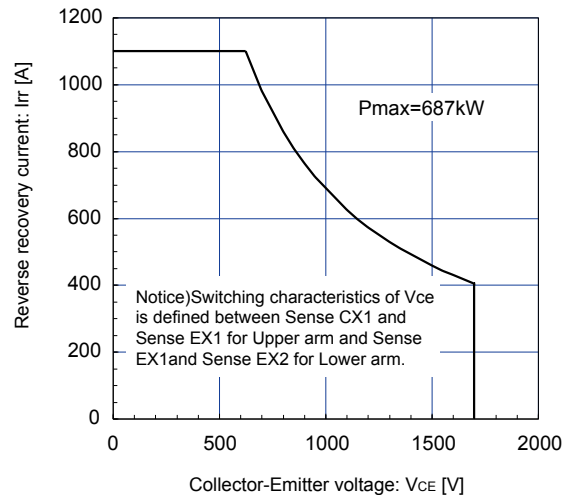
[THERMISTOR]

Temperature characteristic (typ.)

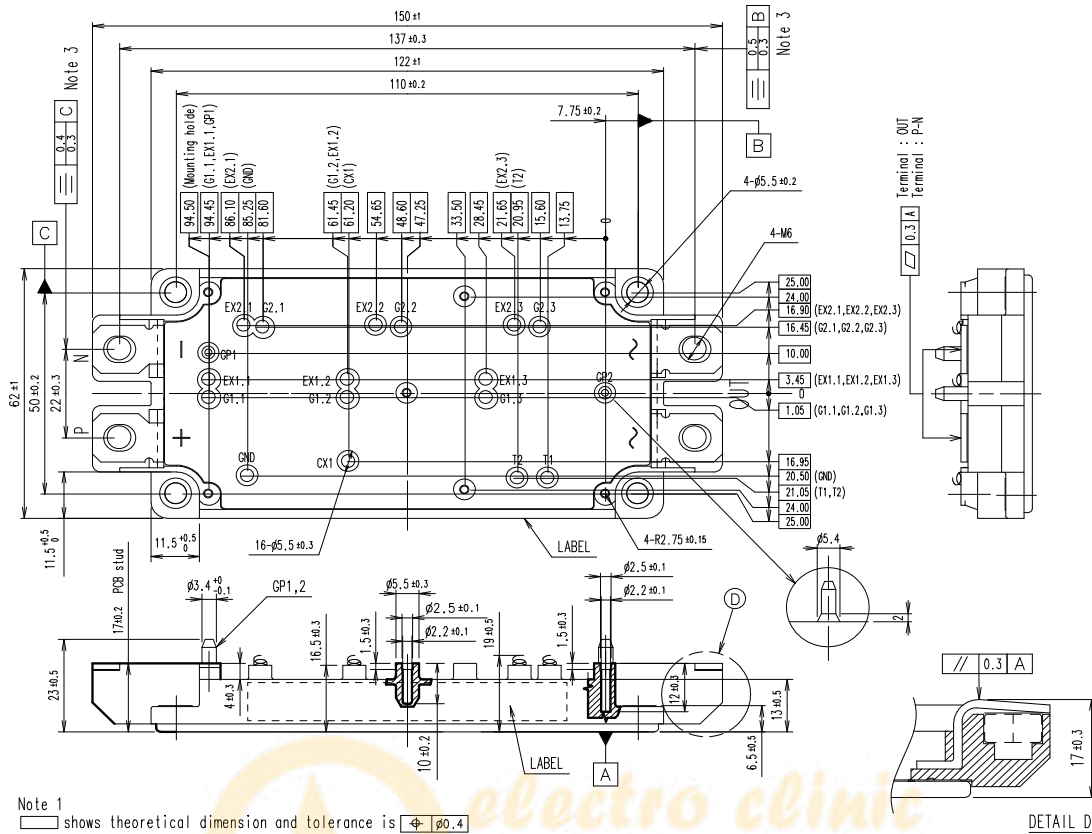


FWD safe operating area (max.)

$T_J=150^\circ C$



Outline Drawings(Unit:mm)



Note 1
 shows theoretical dimension and tolerance is $\pm \phi 0.4$

Note 2
 Rule for PCB
 · Guide pin hole : $\phi 4.0 \pm 0.1$
 · Guide pin distance : 94.45 ± 0.1
 · Spring contact pad : $\phi 3.8 \pm 0.2$
 · Position tol.pad : $\pm \phi 1 \phi 0.4$

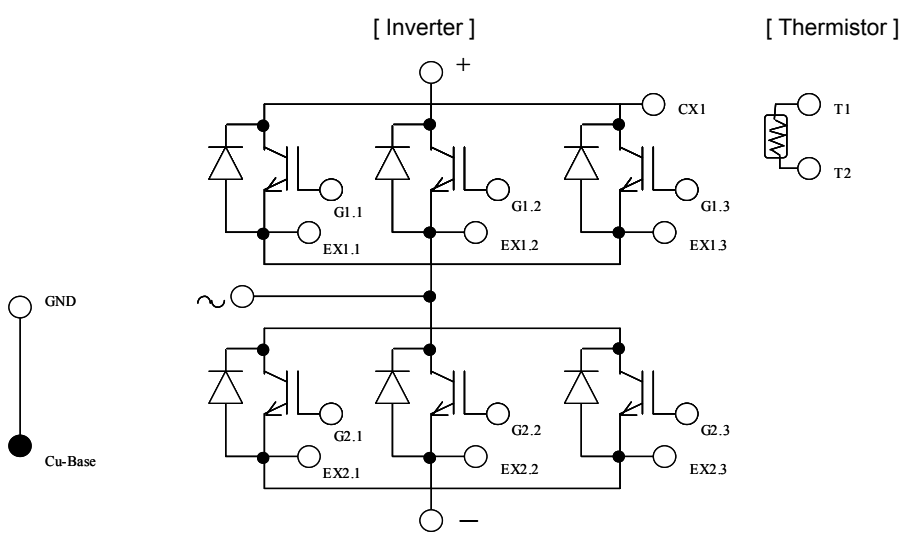
Note 3

± 0.3	B
± 0.4	C

 Upper value : Terminal hole center
 Lower value : Nut center
 (Including margin of the nut position.)

Weight: 360g (typ.)

Equivalent Circuit



WARNING

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